

ABSTRACT OF THE DISCLOSURE

A magnetic memory device includes a first  
interconnection which runs in a first direction, a  
second interconnection which runs in a second direction  
5 different from the first direction, a magnetoresistive  
element which is arranged at the intersection of and  
between the first and second interconnections, and a  
metal layer which is connected to the magnetoresistive  
element and has a side surface that partially coincides  
10 with a side surface of the magnetoresistive element.